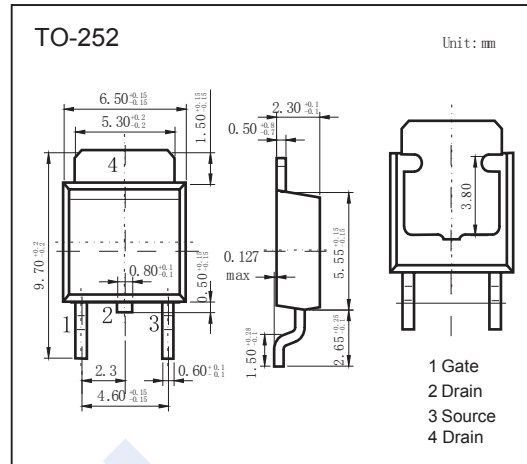
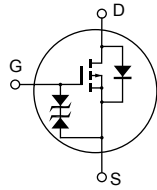


P-Channel MOSFET

2SJ181S

■ Features

- $V_{DS} = -600V$
- $I_D = -0.5 A$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 25 \Omega$ ($V_{GS} = -10V$)
- High speed switching
- Low drive current



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-600	V
Gate-Source Voltage	V_{GS}	± 15	
Continuous Drain Current	I_D	-0.5	A
Pulsed Drain Current (Note.1)	I_{DM}	-1	
Body to Drain Diode Reverse Drain Current	I_{DR}	-0.5	
Power Dissipation $T_c = 25^\circ C$	P_D	20	W
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

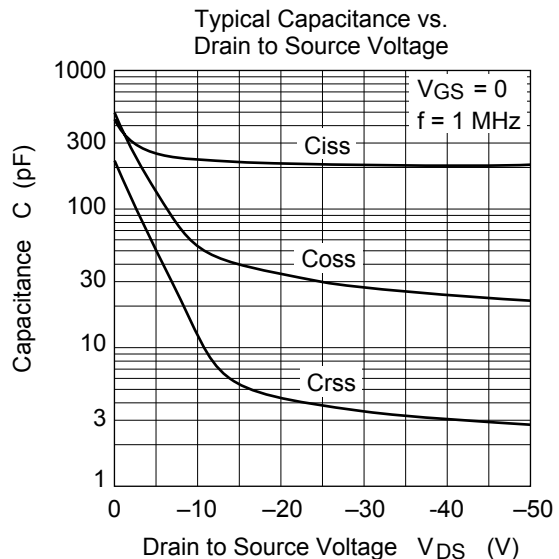
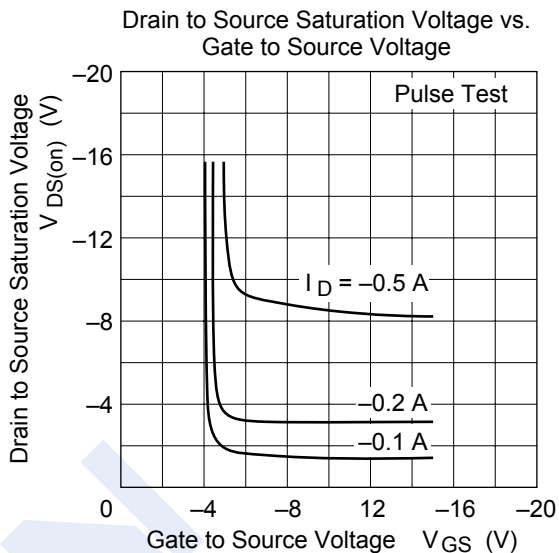
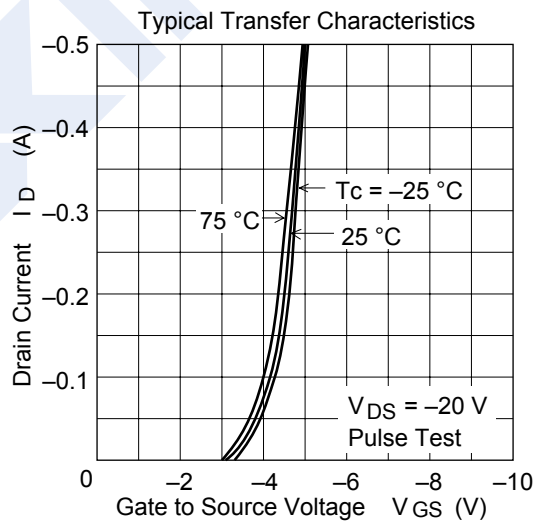
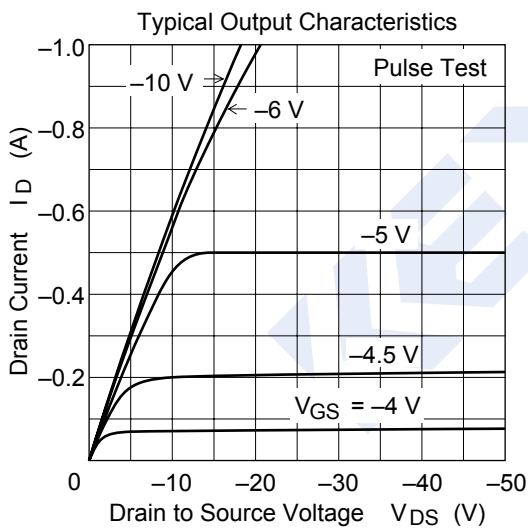
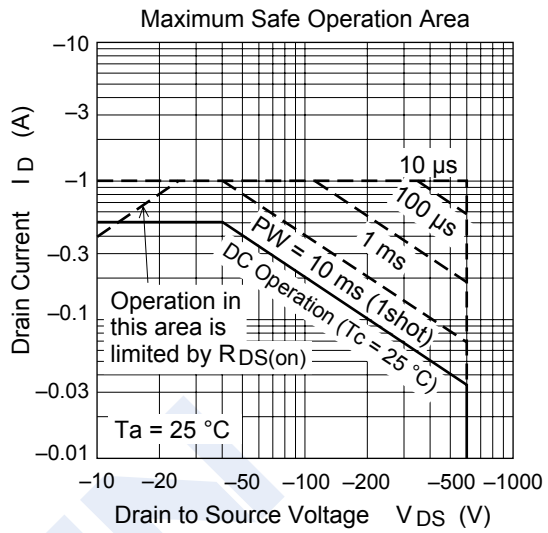
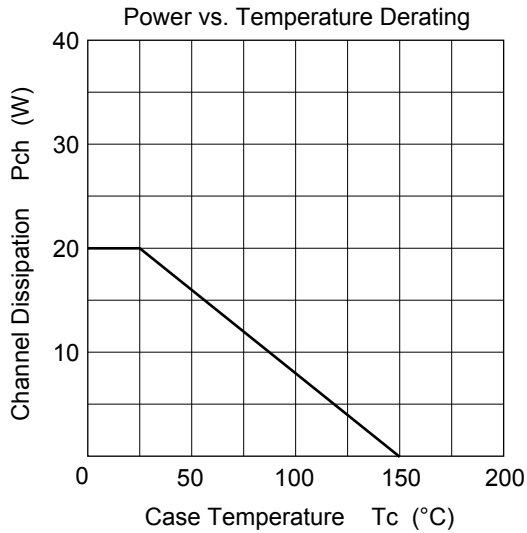
Note.1: $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -10mA, V_{GS} = 0V$	-600			V
Gate to Source Breakdown Voltage	V_{GSS}	$I_G = \pm 100 \mu A, V_{DS} = 0V$	± 15			
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -500V, V_{GS} = 0V$			-100	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$			± 10	μA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -10V, I_D = -1mA$	-2		-4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -0.3A$			25	Ω
Forward Transconductance	g_{FS}	$V_{DS} = -20V, I_D = -0.3A$	0.3	0.45		S
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$		220		pF
Output Capacitance	C_{oss}			55		
Reverse Transfer Capacitance	C_{rss}			13		
Turn-On DelayTime	$t_{d(on)}$		$V_{GS} = -10V, I_D = -0.3A, R_L = 100 \Omega$		7	
Turn-On Rise Time	t_r			20		
Turn-Off DelayTime	$t_{d(off)}$			35		
Turn-Off Fall Time	t_f			35		
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -0.5A, V_{GS} = 0, di/dt = 50A/\mu s$		230		
Diode Forward Voltage	V_{SD}	$I_S = -0.5A, V_{GS} = 0V$		-0.85		V

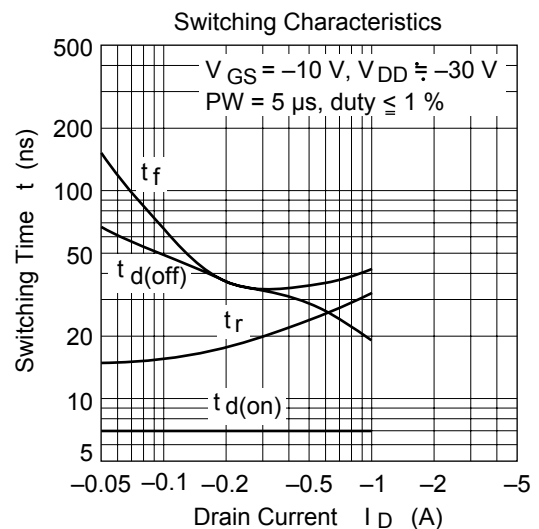
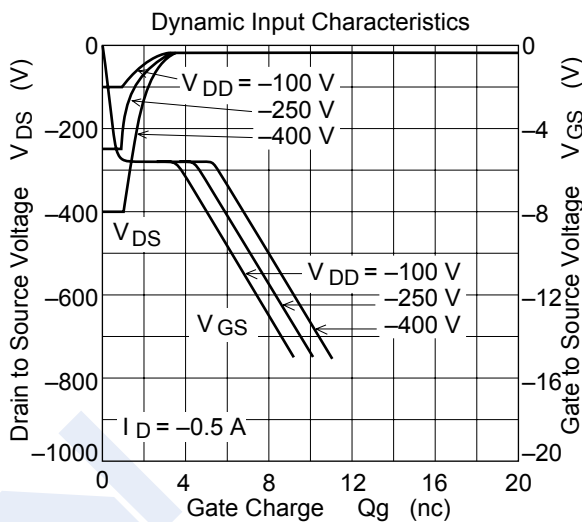
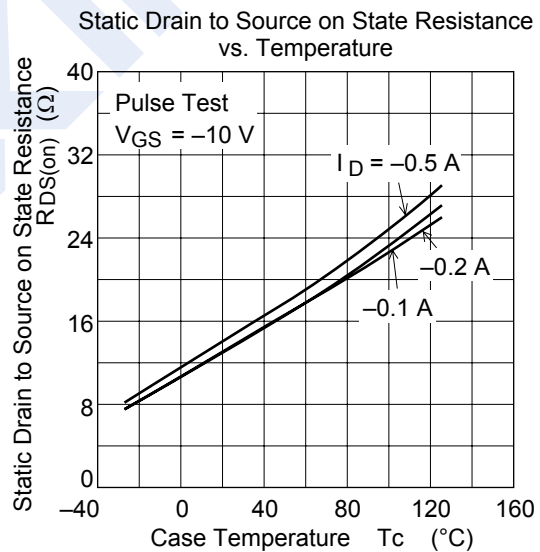
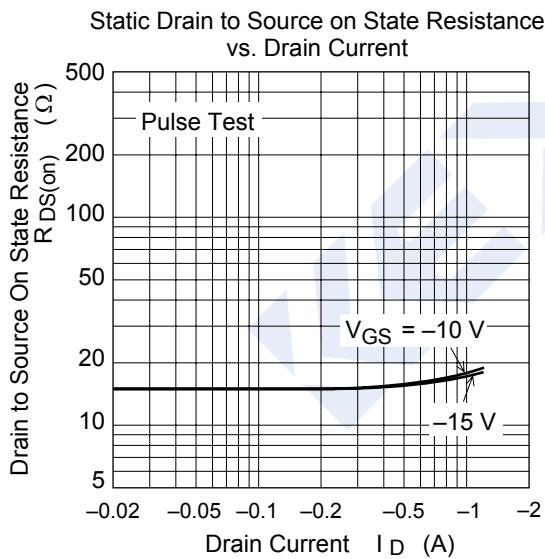
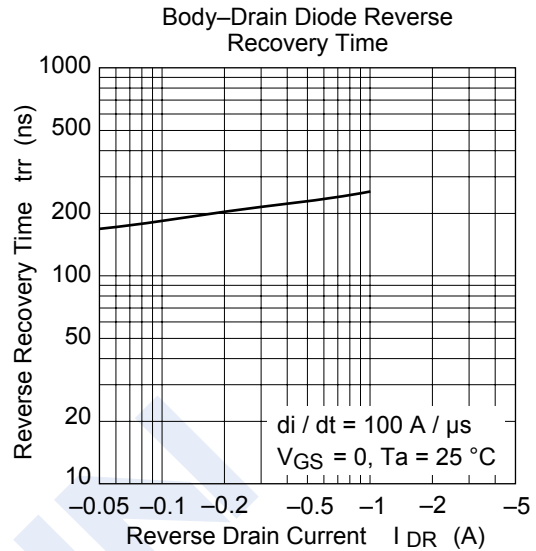
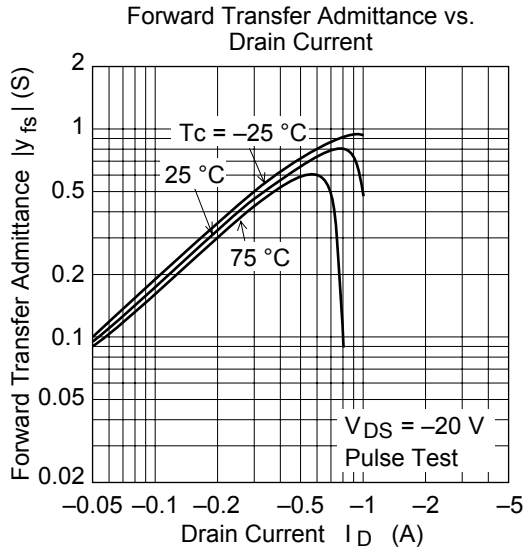
P-Channel MOSFET 2SJ181S

■ Typical Characteristics



P-Channel MOSFET 2SJ181S

■ Typical Characteristics



P-Channel MOSFET 2SJ181S

■ Typical Characteristics

